

The RF Line

NPN Silicon

RF Power Transistors

... designed for 24 volt UHF large-signal, common-emitter amplifier applications in industrial and commercial FM equipment operating in the range of 800–960 MHz.

- Specified 24 Volt, 900 MHz Characteristics
 - Output Power = 5.0 Watts
 - Power Gain = 9.0 dB Min
 - Efficiency = 50% Min
- Series Equivalent Large-Signal Characterization
- Capable of Withstanding 20:1 VSWR Load Mismatch at Rated Output Power and Supply Voltage
- Gold Metallized, Emitter Ballasted for Long Life and Resistance to Metal Migration
- Silicon Nitride Passivated
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	V_{CEO}	30	Vdc
Collector–Emitter Voltage	V_{CES}	55	Vdc
Emitter–Base Voltage	V_{EBO}	4.0	Vdc
Collector Current — Continuous	I_C	0.6	Adc
Total Device Dissipation @ $T_A = 50^\circ\text{C}$ (1) Derate above 50°C	P_D	18 0.143	Watts W/ $^\circ\text{C}$
Storage Temperature Range	T_{stg}	–65 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case (2)	$R_{\theta JC}$	7.0	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector–Emitter Breakdown Voltage ($I_C = 20\text{ mAdc}$, $I_B = 0$)	$V_{(BR)CEO}$	30	—	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 20\text{ mAdc}$, $V_{BE} = 0$)	$V_{(BR)CES}$	55	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 0.5\text{ mAdc}$, $I_C = 0$)	$V_{(BR)EBO}$	4.0	—	—	Vdc
Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $V_{BE} = 0$, $T_C = 25^\circ\text{C}$)	I_{CES}	—	—	1.0	mAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 200\text{ mAdc}$, $V_{CE} = 5.0\text{ Vdc}$)	h_{FE}	30	—	150	—
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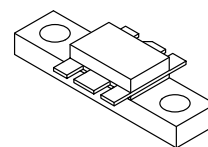
NOTES:

- This device is designed for RF operation. The total device dissipation rating applies only when the device is operated as an RF amplifier.
- Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

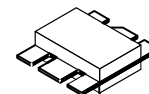
(continued)

MRF891
MRF891S

5.0 W, 900 MHz
RF POWER
TRANSISTORS
NPN SILICON



CASE 319-07, STYLE 2
MRF891



CASE 319A-02, STYLE 2
MRF891S



ELECTRICAL CHARACTERISTICS — continued ($T_C = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS					
Output Capacitance ($V_{CB} = 24\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{ob}	—	6.5	8.0	pF
FUNCTIONAL TESTS					
Common-Emitter Amplifier Power Gain (Broadband) ($V_{CC} = 24\text{ Vdc}$, $P_{out} = 5.0\text{ W}$, $f = 900\text{ MHz}$)	G_{pe}	9.0	10	—	dB
Collector Efficiency ($V_{CC} = 24\text{ Vdc}$, $P_{out} = 5.0\text{ W}$, $f = 900\text{ MHz}$)	η	50	57	—	%
Load Mismatch Stress ($V_{CC} = 24\text{ Vdc}$, $P_{in} = 0.63\text{ W}$, $f = 900\text{ MHz}$, $VSWR = 20:1$, all phase angles)	ψ	No Degradation in Output Power			

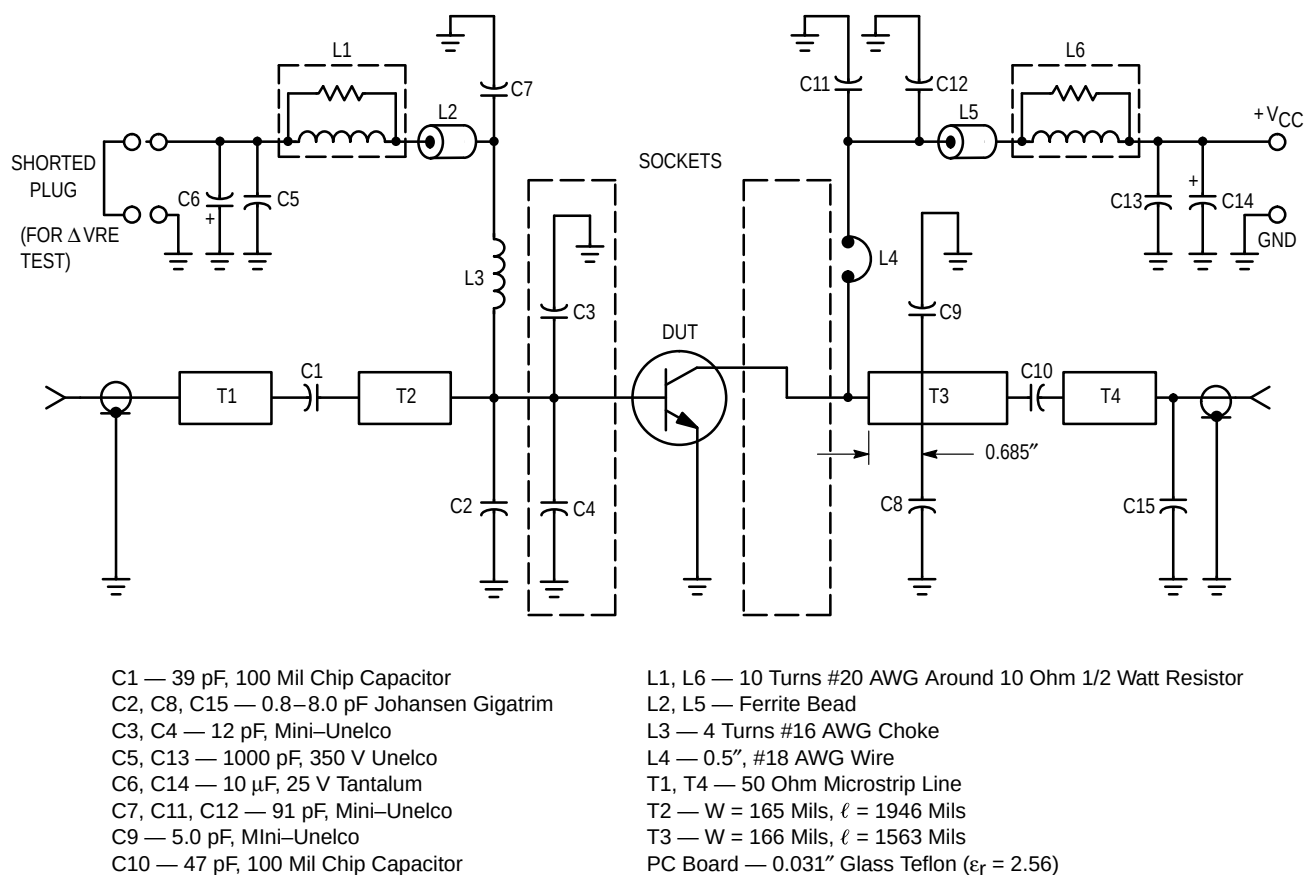


Figure 1. Broadband Test Fixture

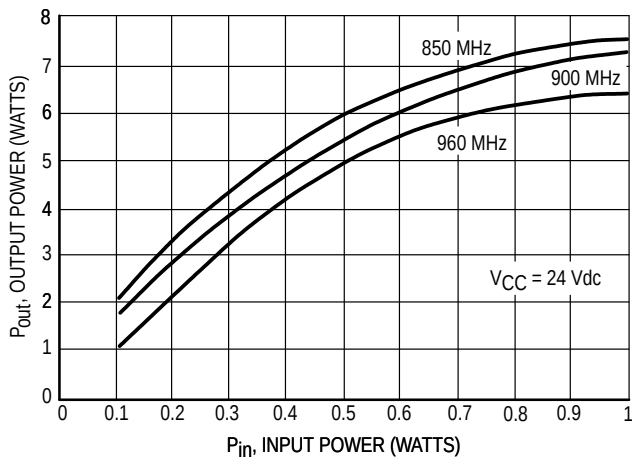


Figure 2. Output Power versus Input Power

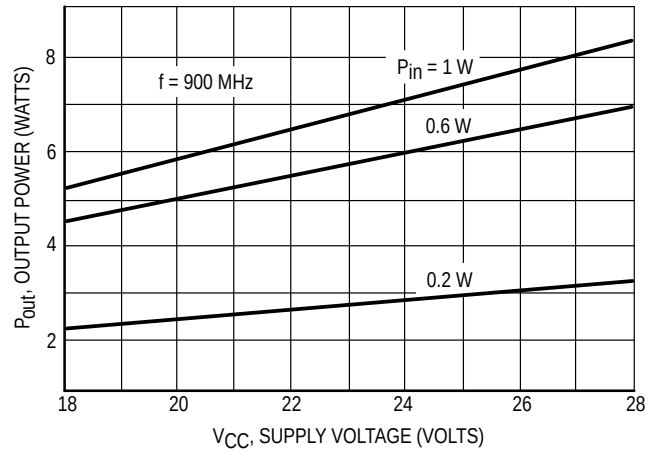


Figure 3. Output Power versus Supply Voltage

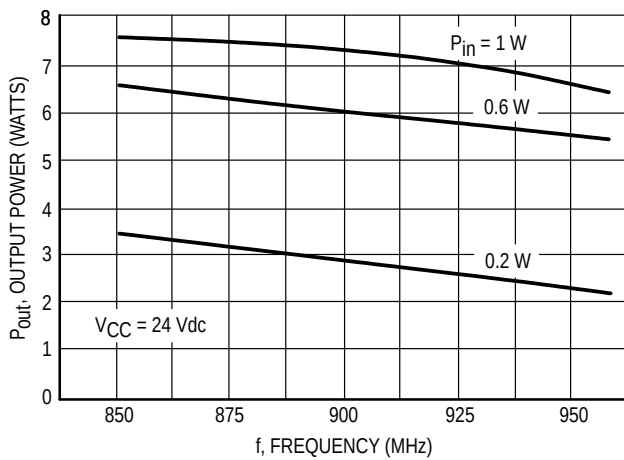


Figure 4. Output Power versus Frequency

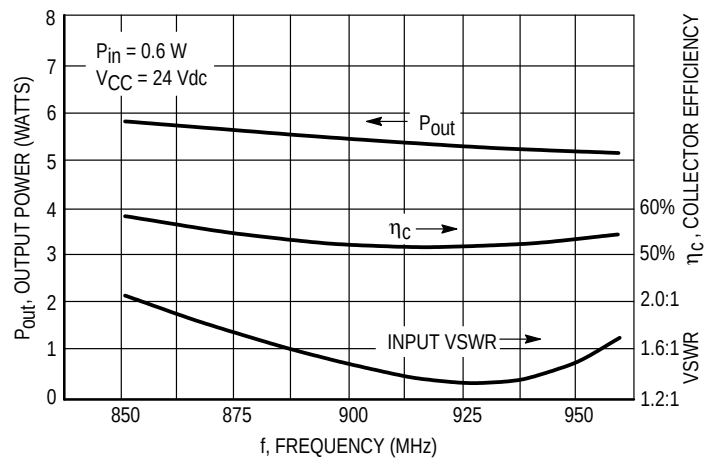


Figure 5. Typical Broadband Circuit Performance

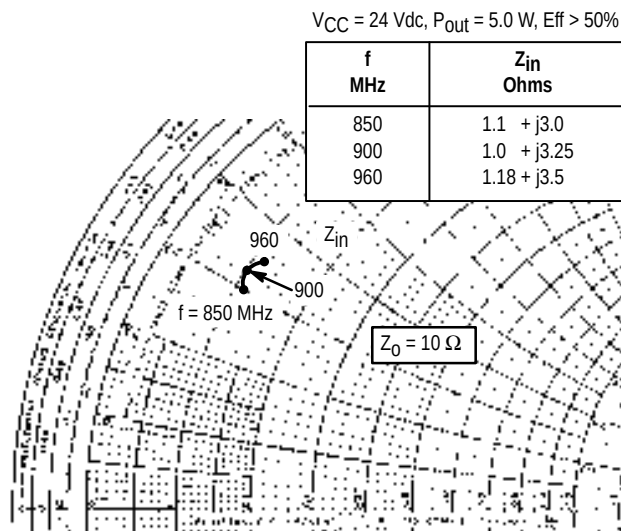


Figure 6. Series Equivalent Input Impedance

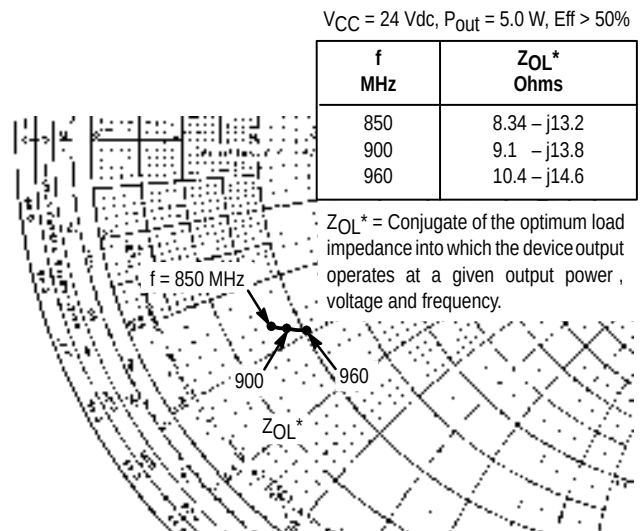
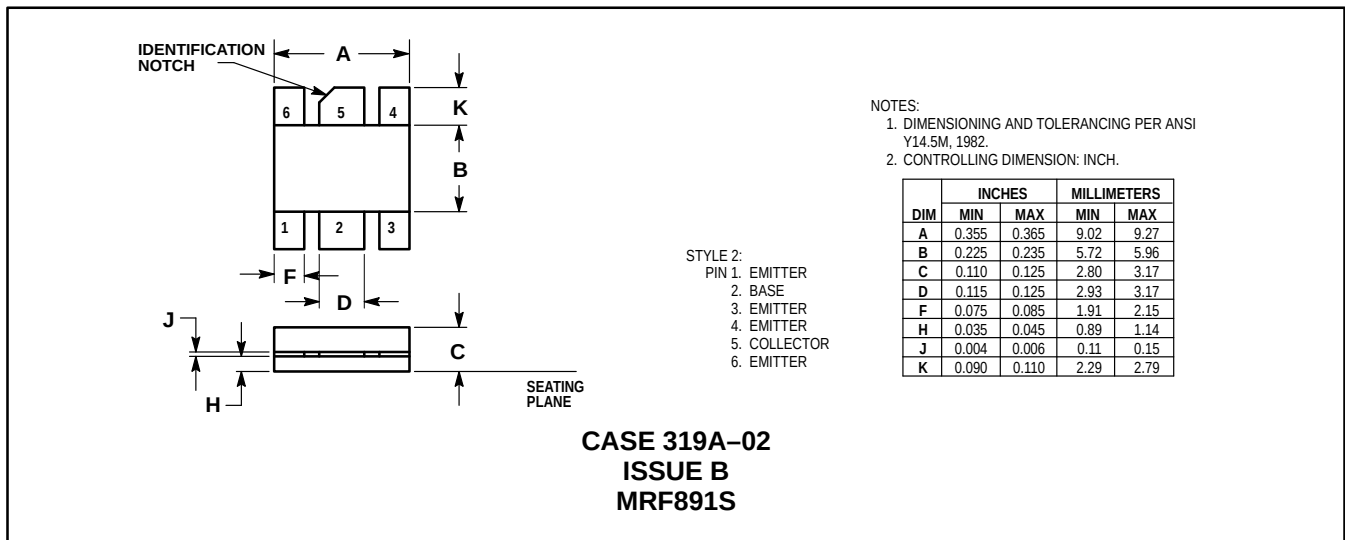
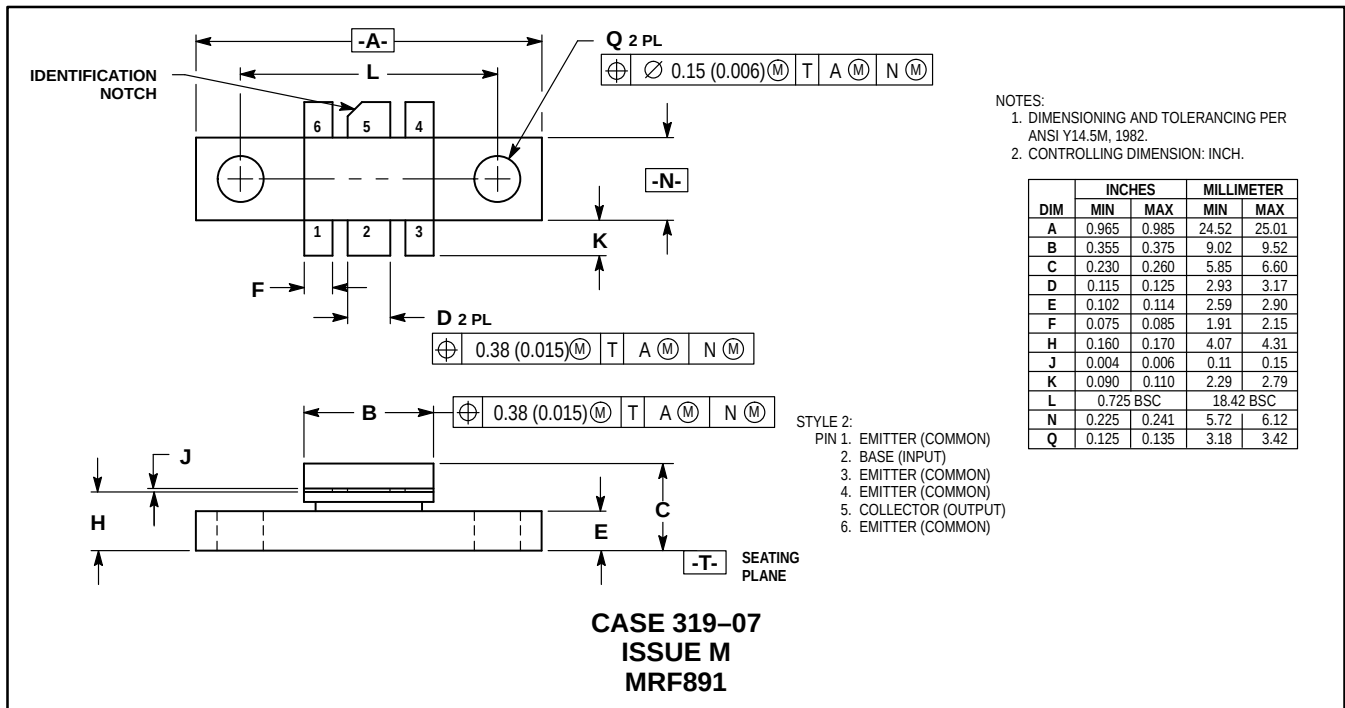


Figure 7. Series Equivalent Output Impedance

PACKAGE DIMENSIONS



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